



DMG3414U

N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- $25m\Omega$ @ $V_{GS} = 4.5V$
- $29m\Omega$ @ $V_{GS} = 2.5V$
- $37m\Omega$ @ $V_{GS} = 1.8V$
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMG3414UQ)

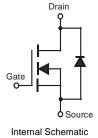
Mechanical Data

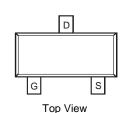
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208@3
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)





Top View





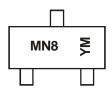
Ordering Information (Note 4)

Part Number	Case	Packaging
DMG3414U-7	SOT23	3.000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



MN8 = Product Type Marking Code $Y \text{ or } \overline{Y} = \text{Year (ex: E} = 2017)$ M = Month (ex: 9 = September)

Date Code Key

Year	2009	•	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	W	-	Е	F	G	Ι	-	J	K	L	М

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Charact	eristic		Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current (Note 5)	T _A = +25°C T _A = +70°C	I _D	4.2 3.2	А	
Pulsed Drain Current (Note 6)			I _{DM}	30	А

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	0.78	W
Thermal Resistance, Junction to Ambient @T _A = +25°C	R _{θJA}	162	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

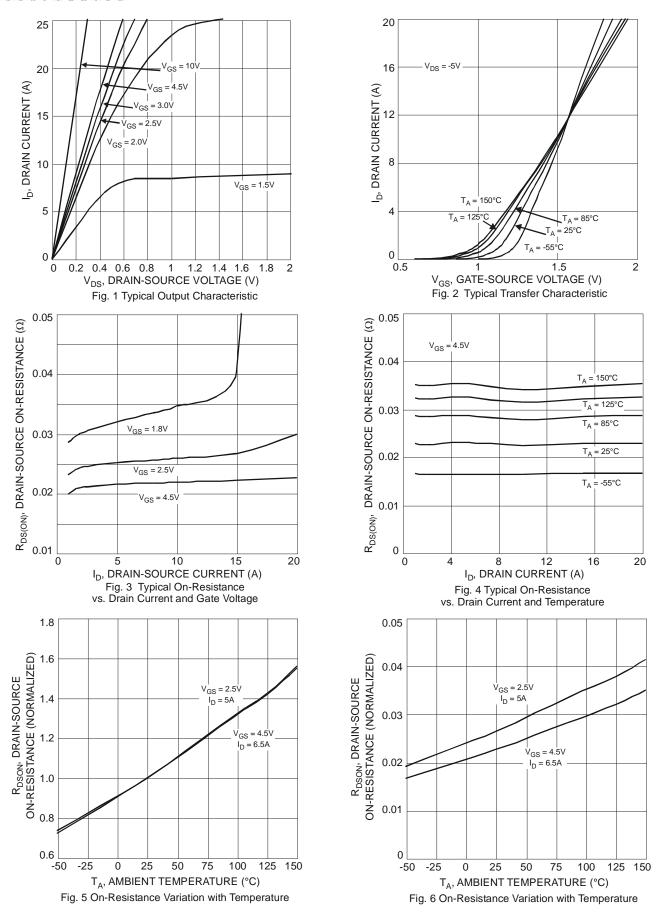
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 7)								
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$		
Zero Gate Voltage Drain Current T _J = +25°C	: I _{DSS}	_	_	1.0	μΑ	V _{DS} = 20V, V _{GS} = 0V		
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 8V$, $V_{DS} = 0V$		
ON CHARACTERISTICS (Note 7)								
Gate Threshold Voltage	V _{GS(TH)}	0.5	_	0.9	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$		
			19	25		$V_{GS} = 4.5V, I_D = 8.2A$		
Static Drain-Source On-Resistance	R _{DS(ON)}	_	22	29	mΩ	$V_{GS} = 2.5V, I_D = 3.3A$		
			28	37		$V_{GS} = 1.8V, I_D = 2.0A$		
Forward Transfer Admittance	Y _{FS}	_	7	_	S	$V_{DS} = 10V, I_{D} = 4A$		
Diode Forward Voltage	V _{SD}	_	0.6	1	V	V _{GS} = 0V, I _S = 1A		
DYNAMIC CHARACTERISTICS (Note 8)	<u> </u>							
Input Capacitance	C _{ISS}	_	829.9	_	pF			
Output Capacitance	Coss	_	85.3	_	pF	$V_{DS} = 10V, V_{GS} = 0V$ - f = 1.0MHz		
Reverse Transfer Capacitance	C _{RSS}	_	81.2	_	pF	1 - 1.00012		
Total Gate Charge	Q _G	_	9.6	_	nC			
Gate-Source Charge	Q _{GS}	_	1.5	_	nC	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 8.2A		
Gate-Drain Charge	Q _{GD}	_	3.5	_	nC			
Turn-On Delay Time	t _{D(ON)}	_	8.1	_	ns			
Turn-On Rise Time	t _R	_	8.3	_	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$		
Turn-Off Delay Time	t _{D(OFF)}	_	40.1	_	ns	$R_L = 10\Omega$, $R_G = 6\Omega$, $I_D = 1A$		
Turn-Off Fall Time	t _F	_	9.6	_	ns	7		

Notes:

- 5. Device mounted on FR-4 PCB with 2oz. Copper and test pulse width $t \le 10s$.
- 6. Repetitive rating, pulse width limited by junction temperature. 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to production testing.







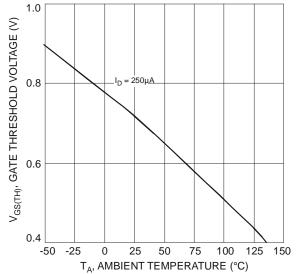
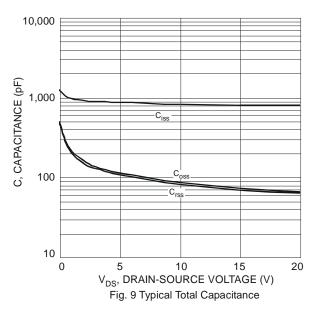
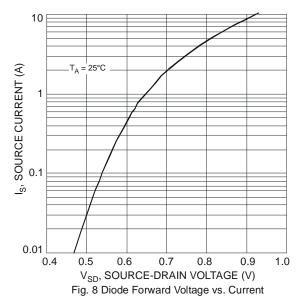


Fig. 7 Gate Threshold Variation vs. Ambient Temperature





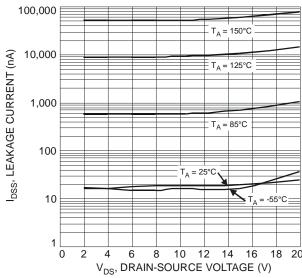


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

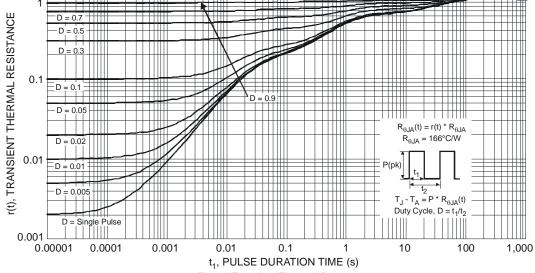


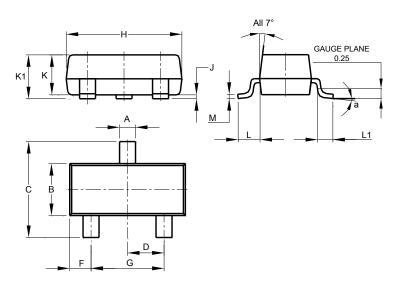
Fig. 11 Transient Thermal Response



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

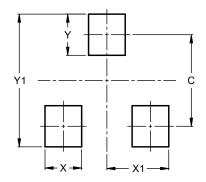


SOT23								
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
7	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K 1	0.903	1.10	1.025					
٦	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
М	0.085	0.150	0.110					
а	0°	8°						
All	Dimens	ions in	mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
X	0.8
X1	1.35
Y	0.9
V1	2.0



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